



- Notes:**
- REVA**
- 1. Need to break Inductor pad into 4 to accomediate GaN PL backup solution.
 - 2. Tie Vbat- and SGND together only at LM5177 pin 30 and PAD.
 - 3. Inductor sample provided by customer
 - 4. GaN team to recommend HB1 and HB2 diodes
 - 5. BSC devices on bottom side, Heatsink? Increase current capability?



Notes:
REVA
1. In parallel GaNFETs

